

Title (en)

SHIELDING OF ANALOG CIRCUITS ON SEMICONDUCTOR SUBSTRATES

Title (de)

ABSCHIRMUNG ANALOGER SCHALTKREISE AUF EINEM HALBLEITERSUBSTRAT

Title (fr)

BLINDAGE DE CIRCUITS ANALOGIQUES SUR DES SUBSTRATS SEMICONDUCTEURS

Publication

**EP 1287554 A2 20030305 (EN)**

Application

**EP 01946084 A 20010605**

Priority

- US 0118153 W 20010605
- US 58824300 A 20000606

Abstract (en)

[origin: WO0195389A2] A semiconductor device, in accordance with the present invention, includes a doped semiconductor substrate (102) wherein the doping of the substrate has a first conductivity and a device region (110) formed near a surface of the substrate. The device region includes at least one device well. A buried well (104) is formed in the substrate below the device region. The buried well is doped with dopants having a second conductivity. A trench region (124) surrounds the device region and extends below the surface of the substrate to at least the buried well such that the device region is isolated from other portions of the substrate by the buried well and the trench region.

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**H01L 21/761**

IPC 8 full level

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CPC (source: EP KR)

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